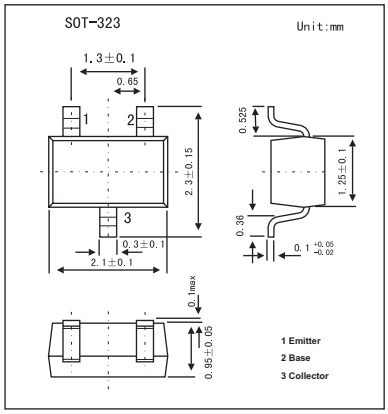
Silicon PNP Epitaxial Planar Type

2SB1219



■ Features

● Large collector current IC.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-25	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-1	A
Collector current	I_C	-500	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = -10 □A, I_E = 0	-30			V
Collector-emitter voltage	V_{CEO}	I_C = -2 mA, I_B = 0	-25			V
Emitter-base voltage	V_{EBO}	I_E = -10 □A, I_C = 0	-5			V
Collector-base cutoff current	I_{CBO}	V_{CB} = -20 V, I_E = 0			-0.1	μA
Forward current transfer ratio	h_{FE}	V_{CE} = -10 V, I_C = -150 mA	85		340	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -300 mA, I_B = -30 mA		-0.35	-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = -300 mA, I_B = -30 mA		-1.1	-1.5	
Transition frequency	f_T	V_{CB} = -10 V, I_E = 50 mA, f = 200 MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0, f = 1 MHz		6	15	pF

■ hFE Classification

Marking	CQ	CR	CS	C
h_{FE}	85～170	120～240	170～340	85～340